

Silicon Schottky Diode

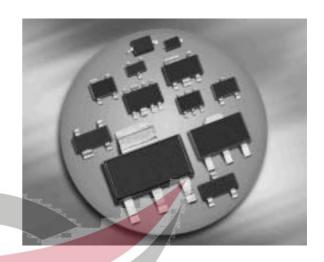
- High current rectifier Schottky diode with very low V_F drop (typ. 0.24 V at I_F = 10mA)
- For power supply applications
- For clamping and protection in low voltage applications
- For detection and step-up-conversion
- Pb-free (RoHS compliant) package 1)
- Qualified according AEC Q101





BAT60B





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

| Туре | Package | Configuration | Marking |
|--------|---------|---------------|---------|
| BAT60B | SOD323 | single | white/5 |

Maximum Ratings at $T_A = 25$ °C, unless otherwise specified

| Parameter | Symbol | Value | Unit |
|---|------------------|---------|------|
| Diode reverse voltage ²⁾ | V_{R} | 10 | V |
| Forward current | /F | 3 | Α |
| Non-repetitive peak surge forward current | I _{FSM} | 5 | |
| (t ≤ 10ms) | LEC | TRONIC | |
| Total power dissipation | P _{tot} | 1350 | mW |
| <i>T</i> _S ≤ 28°C | | | |
| Junction temperature | $ T_{j} $ | 150 | °C |
| Operating temperature range | T_{op} | -55 125 | |
| Storage temperature | $T_{\rm stg}$ | -55 150 | |

¹Pb-containing package may be available upon special request

 $^{^2}$ For $T_A > 25$ $^{\circ}$ C the derating of V_R has to be considered. Please refer to curve Permissible reverse voltage.



| Th | erm | al | Re | eie | eta | nce |
|----|-----|----|----|------|-----|------|
| | enn | aı | NE | :51: | sla | IICE |

| Parameter | Symbol | Value | Unit |
|--|-------------------|-------|------|
| Junction - soldering point ¹⁾ | R _{thJS} | ≤ 90 | K/W |

Electrical Characteristics at $T_{\Lambda} = 25^{\circ}\text{C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|--|----------------|--------|------|------|------|
| | | min. | typ. | max. | |
| DC Characteristics | | | | | |
| Reverse current ²⁾ | I _R | | | | μΑ |
| V _R = 5 V | | - | 5 | 15 | |
| $V_{R} = 8 V$ | | | 10 | 25 | |
| $V_{R} = 5 \text{ V}, T_{A} = 80 \text{ °C}$ | | - | 100 | 800 | |
| $V_{R} = 8 \text{ V}, T_{A} = 80 \text{ °C}$ | | | 410 | 1500 | |
| Forward voltage ²⁾ | V_{F} | | | | V |
| <i>I</i> _F = 10 mA | | 0.2 | 0.24 | 0.3 | |
| <i>I</i> _F = 100 mA | | 0.26 | 0.32 | 0.38 | |
| $I_{\rm F} = 500 \text{mA}$ | | 0.32 | 0.4 | 0.5 | |
| $I_{\rm F} = 1000 \text{mA}$ | | 0.36 | 0.48 | 0.6 | |
| AC Characteristics | | | | | |
| Diode capacitance | C_{T} | 12 | 25 | 30 | pF |
| $V_{R} = 5 \text{ V}, f = 1 \text{ MHz}$ | | | | | |

¹For calculation of R_{thJA} please refer to Application Note Thermal Resistance

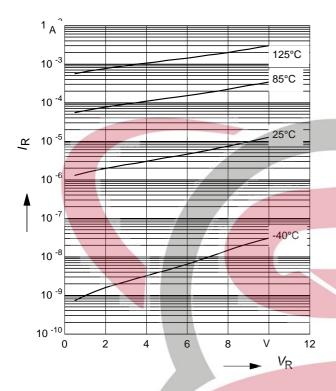
²Pulsed test: $t_p = 300 \,\mu\text{s}$; D = 0.01





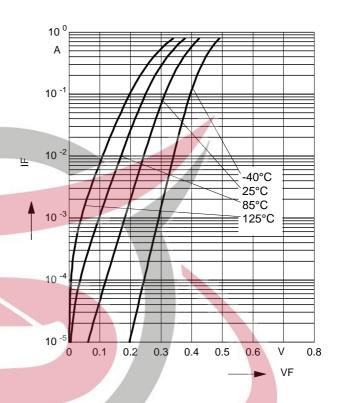
Reverse current $I_R = f(V_R)$

 T_A = Parameter



Forward current $I_F = f(V_F)$

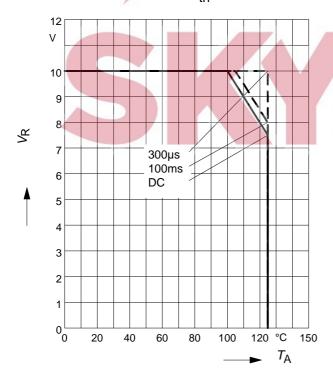
 T_A = Parameter



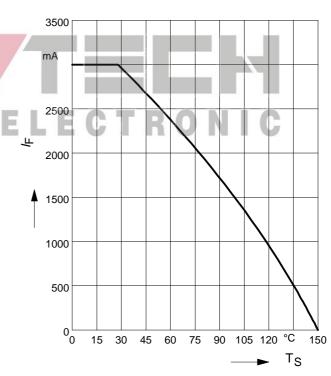
Permissible Reverse voltage $V_R = f(T_A)$

 t_p = Parameter; duty cycle < 0.01

Device mounted on PCB with $R_{th} = 160 \text{ K/W}$



Forward current $I_F = f(T_S)$

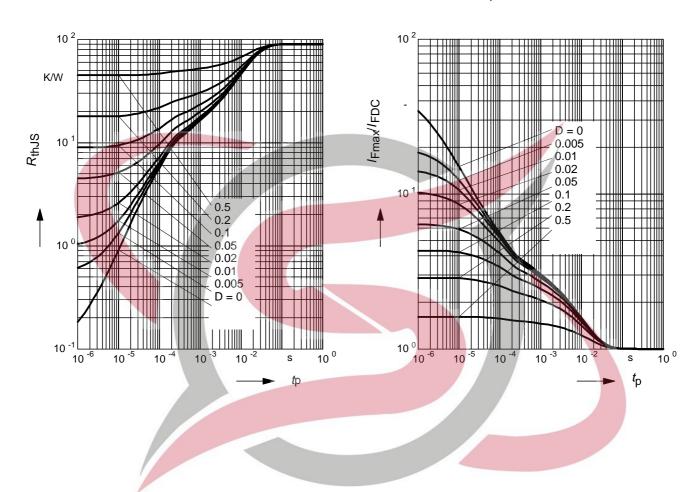




Permissible Puls Load $R_{thJS} = f(t_p)$

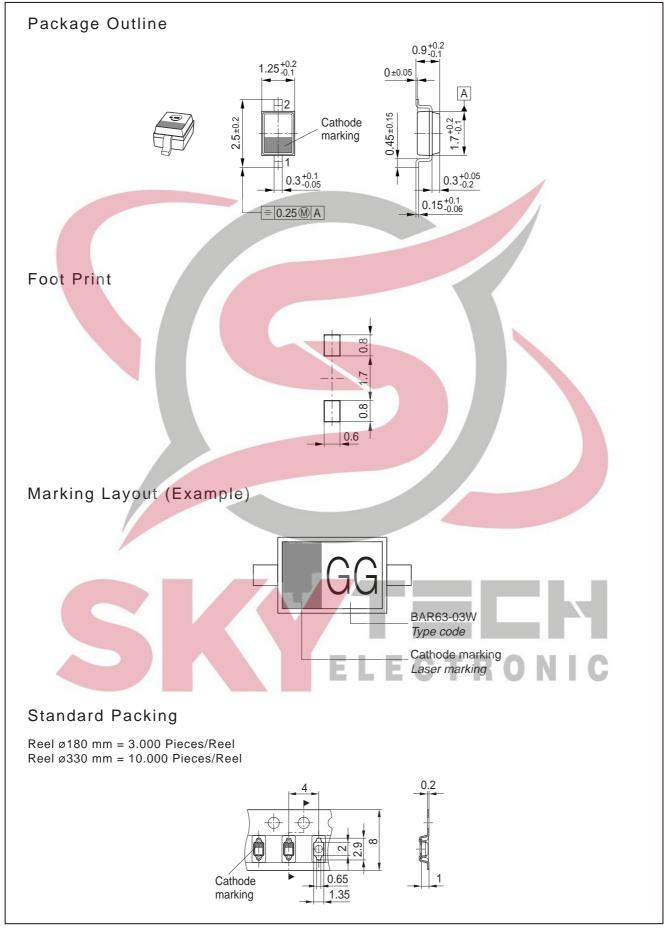
Permissible Pulse Load

$$I_{\text{Fmax}}/I_{\text{FDC}} = f(t_{\text{p}})$$



S TECH ELECTRONIC







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